

AUTHOR CORRECTION

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Author Correction: Graphene-driving strain engineering to enable strain-free epitaxy of AlN film for deep ultraviolet light-emitting diode

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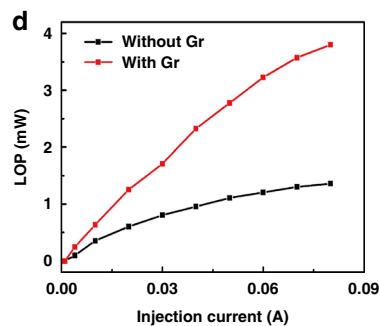
Correction to: *Light Science & Applications*
<https://doi.org/10.1038/s41377-022-00756-1>
published online 07 April 2022

The original article has been updated.

Following publication of this article¹, it is noticed Fig. 6d contained a typo: the unit of x-coordinate should be A, not mA.

The correct Fig. 6d is provided in this Correction.

Published online: 29 April 2022



Reference

1. Chang, H., Liu, Z. & Yang, S. et al. Graphene-driving strain engineering to enable strain-free epitaxy of AlN film for deep ultraviolet light-emitting diode. *Light Sci. Appl.* **11**, 88 (2022).

